

TIP29A/29C TIP30A/30C

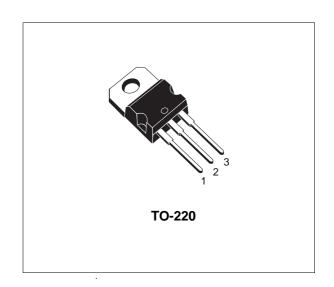
COMPLEMENTARY SILICON POWER TRANSISTORS

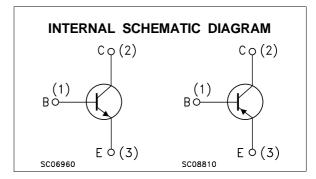
- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES

DESCRIPTION

The TIP29A and TIP29C are silicon Epitaxial-Base NPN power transistors mounted in Jedec TO-220 plastic package. They are intented for use in medium power linear and switching applications.

The complementary PNP types are TIP30A and TIP30C respectively.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Va	Unit	
		NPN	TIP29A	TIP29C	
		PNP	TIP30A	TIP30C	
V _{CBO}	Collector-Base Voltage (I _E = 0)		60	100	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		60	100	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)		5		V
Ic	Collector Current		1		Α
I _{CM}	Collector Peak Current		3		Α
lΒ	Base Current		0.4		Α
P _{tot}	Total Dissipation at T _{case} ≤ 25 °C		3	0	W
	T _{amb} ≤ 25 °C		2	2	W
T _{stg}	Storage Temperature		-65 to 150		°C
Tj	Max. Operating Junction Temperature		15	°C	

For PNP types voltage and current values are negative.

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TIP29A / TIP29C / TIP30A / TIP30C

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	4.17	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

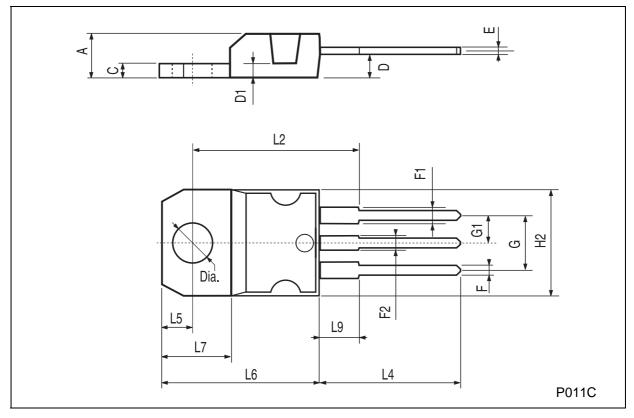
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CEO}	Collector Cut-off Current (I _B = 0)	for TIP29A/30A			0.3 0.3	mA mA
ICES	Collector Cut-off Current (V _{BE} = 0)	for TIP29A/30A			0.2 0.2	mA mA
I _{EBO}	Emitter Cut-off Current (Ic = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for TIP29A/30A for TIP29C/30C	60 100			V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_C = 1 \text{ A}$ $I_B = 125 \text{ mA}$			0.7	V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 1 A V _{CE} = 4 V			1.3	V
h _{FE} *	DC Current Gain	$\label{eq:controller} \begin{array}{lll} I_C = 0.2 \ A & V_{CE} = 4 \ V \\ I_C = 1 \ A & V_{CE} = 4 \ V \end{array}$	40 15		75	
h _{fe}	Small Signal Current Gain	$\begin{split} I_{C} &= 0.2 \; A V_{CE} = 10 \; V & f = 1 \; KHz \\ I_{C} &= 0.2 \; A V_{CE} = 10 \; V & f = 1 \; MHz \end{split}$	20 3			

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^{*} Pulsed: Pulse duration = 300 μ s, duty cycle \leq 2 % For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	4.40		4.60	0.173		0.181	
С	1.23		1.32	0.048		0.051	
D	2.40		2.72	0.094		0.107	
D1		1.27			0.050		
Е	0.49		0.70	0.019		0.027	
F	0.61		0.88	0.024		0.034	
F1	1.14		1.70	0.044		0.067	
F2	1.14		1.70	0.044		0.067	
G	4.95		5.15	0.194		0.203	
G1	2.4		2.7	0.094		0.106	
H2	10.0		10.40	0.393		0.409	
L2		16.4			0.645		
L4	13.0		14.0	0.511		0.551	
L5	2.65		2.95	0.104		0.116	
L6	15.25		15.75	0.600		0.620	
L7	6.2		6.6	0.244		0.260	
L9	3.5		3.93	0.137		0.154	
DIA.	3.75		3.85	0.147		0.151	



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